# High-Power NPN Silicon Transistor

This transistor is for use as an output device in complementary audio amplifiers to 100–Watts music power per channel.

## Features

- High DC Current Gain  $-h_{FE} = 25-100$  @ I<sub>C</sub> = 7.5 A
- Excellent Safe Operating Area
- Complement to the PNP MJ4502
- Pb-Free Package is Available\*

## MAXIMUM RATINGS

| Rating  | Symbol                            | Value       | Unit      |
|---|-----------------------------------|-------------|-----------|
| Collector-Emitter Voltage   | V <sub>CER</sub>                  | 100         | Vdc       |
| Collector-Base Voltage  | V <sub>CB</sub>                   | 100         | Vdc       |
| Collector-Emitter Voltage   | V <sub>CEO</sub>                  | 90          | Vdc       |
| Emitter-Base Voltage  | V <sub>EB</sub>                   | 4.0         | Vdc       |
| Collector Current   | Ι <sub>C</sub>                    | 30          | Adc       |
| Base Current  | Ι <sub>Β</sub>                    | 7.5         | Adc       |
| Total Device Dissipation @ T <sub>C</sub> = 25°C<br>Derate above 25°C | PD                                | 200<br>1.14 | W<br>₩/°C |
| Operating and Storage Junction<br>Temperature Range                   | T <sub>J</sub> , T <sub>stg</sub> | -65 to +200 | °C        |

### THERMAL CHARACTERISTICS

| Characteristics                      | Symbol        | Max   | Unit |
|--------------------------------------|---------------|-------|------|
| Thermal Resistance, Junction-to-Case | $\theta_{JC}$ | 0.875 | °C/W |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



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## 30 AMPERE POWER TRANSISTOR NPN SILICON 100 VOLTS – 200 WATTS



TO-204AA (TO-3) CASE 1-07 STYLE 1

## MARKING DIAGRAM



| MJ802 | = Device Code       |
|-------|---------------------|
| G     | = Pb–Free Package   |
| A     | = Assembly Location |
| YY    | = Year              |
| WW    | = Work Week         |
| MEX   | = Country of Origin |

### **ORDERING INFORMATION**

| Device | Package             | Shipping         |
|--------|---------------------|------------------|
| MJ802  | TO-204              | 100 Units / Tray |
| MJ802G | TO–204<br>(Pb–Free) | 100 Units / Tray |

\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## **MJ802**

## **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

| Characteristic   | Symbol                | Min | Max        | Unit |
|--|-----------------------|-----|------------|------|
| OFF CHARACTERISTICS  | l                     |     |            | 1    |
| Collector–Emitter Breakdown Voltage<br>( $I_C = 200 \text{ mAdc}, R_{BE} = 100 \Omega$ )   | BV <sub>CER</sub>     | 100 | -          | Vdc  |
| Collector-Emitter Sustaining Voltage (Note 1) (I <sub>C</sub> = 200 mAdc)  | V <sub>CEO(sus)</sub> | 90  | -          | Vdc  |
| Collector-Base Cutoff Current<br>( $V_{CB} = 100 \text{ Vdc}, I_E = 0$ )<br>( $V_{CB} = 100 \text{ Vdc}, I_E = 0, T_C = 150^{\circ}\text{C}$ ) | І <sub>СВО</sub>      |     | 1.0<br>5.0 | mAdc |
| Emitter–Base Cutoff Current<br>( $V_{BE} = 4.0 \text{ Vdc}, I_C = 0$ )   | I <sub>EBO</sub>      | _   | 1.0        | mAdc |
| DN CHARACTERISTICS <sup>(1)</sup>  |                       |     |            |      |
| DC Current Gain (Note 1)<br>( $I_C = 7.5 \text{ Adc}, V_{CE} = 2.0 \text{ Vdc}$ )  | h <sub>FE</sub>       | 25  | 100        | -    |
| Base-Emitter "On" Voltage<br>(I <sub>C</sub> = 7.5 Adc, V <sub>CE</sub> = 2.0 Vdc)   | V <sub>BE(on)</sub>   | -   | 1.3        | Vdc  |
| Collector–Emitter Saturation Voltage $(I_C = 7.5 \text{ Adc}, I_B = 0.75 \text{ Adc})$   | V <sub>CE(sat)</sub>  | -   | 0.8        | Vdc  |
| Base–Emitter Saturation Voltage $(I_C = 7.5 \text{ Adc}, I_B = 0.75 \text{ Adc})$  | V <sub>BE(sat)</sub>  | -   | 1.3        | Vdc  |
| DYNAMIC CHARACTERISTICS  | ·                     |     | •          | •    |
| Current Coin Bondwidth Broduct   | 4                     | 2.0 |            |      |

Current Gain - Bandwidth Product MHz 2.0  $f_{\mathsf{T}}$ \_  $(I_{C} = 1.0 \text{ Adc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ MHz})$ 

1. Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  2.0%.

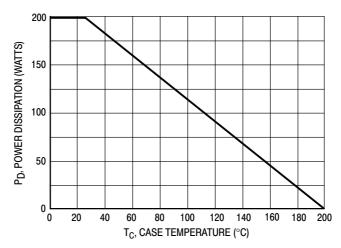
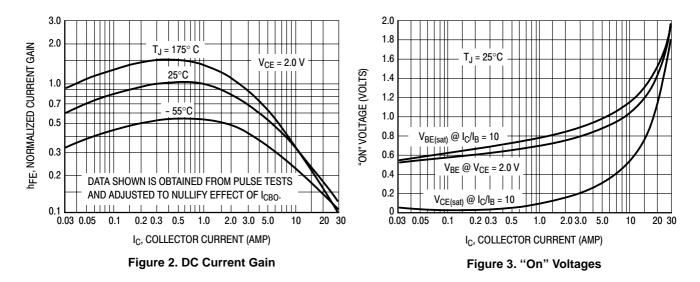


Figure 1. Power–Temperature Derating Curve



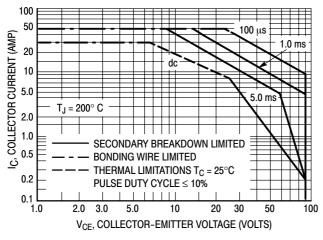


Figure 4. Active Region Safe Operating Area

The Safe Operating Area Curves indicate  $I_C - V_{CE}$  limits below which the device will not enter secondary breakdown. Collector load lines for specific circuits must fall within the applicable Safe Area to avoid causing a catastrophic failure. To insure operation below the maximum  $T_J$ , power temperature derating must be observed for both steady state and pulse power conditions.

## MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



| DIMENSIONS   |   |  |                    |
|--|---|--|--------------------|
| SCALE 1:1  | TO–204 (TO–3)<br>CASE 1–07<br>ISSUE Z   | )  | DATE 05/18/1988    |
| $ \begin{array}{c}                                     $   | $ \begin{array}{c}                                     $  | NOTES:<br>1. DIMENSIONING AND TC<br>Y14.5M, 1982.<br>2. CONTROLLING DIMENS<br>3. ALL RULES AND NOTES<br>REFERENCED TO-204A<br>MIN MAX<br>A 1.550 REF<br>B 1.050<br>C 0.250 0.335<br>D 0.038 0.043<br>E 0.055 0.070<br>G 0.430 BSC<br>H 0.215 BSC<br>K 0.440 0.480<br>L 0.665 BSC<br>N 0.830<br>Q 0.151 0.165<br>U 1.187 BSC<br>V 0.131 0.188 | ION: INCH.         |
| STYLE 1:<br>PIN 1. BASE<br>2. EMITTER<br>CASE: COLLECTOR<br>STYLE 6:<br>PIN 1. GATE<br>2. EMITTER<br>CASE: COLLECTOR | STYLE 2:         STYLE 3:           PIN 1. BASE         PIN 1. GATE           2. COLLECTOR         2. SOURCE           CASE: EMITTER         CASE: DRAIN           STYLE 7:         STYLE 8:           PIN 1. ANODE         PIN 1. CATHODE #1           2. OPEN         2. CATHODE #2           CASE: CATHODE         CASE: ANODE | STYLE 4: STYLE 5:<br>PIN 1. GROUND<br>2. INPUT<br>CASE: OUTPUT<br>STYLE 9:<br>PIN 1. ANODE #1<br>2. ANODE #2<br>CASE: CATHODE  | E<br>AL TRIP/DELAY |

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